line 11, change "BACKGROUND ART" to --2. Description of the Related Art--.

Page 3, line 15, change "DISCLOSURE OF INVENTION" to --SUMMARY OF THE INVENTION--.

Page 5, line 17, change "BEST MODE FOR CARRYING OUT THE INVENTION" to --DETAILED DESCRIPTION OF THE EMBODIMENTS--.

Page 10, line 30, delete "1,2-dimethyloxylene, bis(2-methyloxyethyl)ether,".

Page 11, line 19, delete "These solvents may contain a surface tension modifier, such as a fluorine type, a silicon type, or a nonionic type, in a trace amount, if necessary, within a range which does not impair required functions.".

Page 18, line 29, change "25n" to --65n--.

Page 19, line 1, change "25p" to --65p--;

line 9, change "26n and 26p" to --66n and 66p--.

IN THE CLAIMS:

Please amend claims 1-22 as follows:

1. (Amended) A method for forming a silicon film, comprising:

applying by patterning an ink composition containing a silicon compound onto a substrate by an ink jet process.

2. (Amended) [A] The method for forming a silicon film according to claim 1, [wherein] the ink composition [is] being applied in an inert atmosphere.

3. (Amended) [A] The method for forming a silicon film according to [either] claim 1 [or 2], further comprising[, after applying the ink composition containing the silicon compound onto the substrate by the ink jet process,]: a drying step of removing a solvent of the composition; and

a step of pyrolyzing [an/or] and/or photolyzing in the coating film.

4. (Amended) [A] The method for forming a silicon film according to claim 3, further comprising:

a step for irradiating the silicon film formed by the heat treatment and/or the light treatment with laser to convert the amorphous silicon film into a polycrystalline silicon film.

5. (Amended) [A] The method for forming a silicon film according to claim 1, [wherein] the silicon compound is a silicon compound represented by [the following general formula (I):]

$$Si_nX_m \qquad [(I)]$$

[wherein] n [represents] representing an integer 3 or more, m [represents] representing an integer of n, 2n-2, 2n, or 2n+2, and X [represents] representing a hydrogen atom and/or a halogen atom.

6. (Amended) [A] The method for forming a silicon film according to claim 1, [wherein] the silicon compound is a silicon compound represented by [the following general formula (II):]

$$Si_aX_bY_c \qquad [(II)]$$

[wherein] X [represents] representing a hydrogen atom and/or a halogen atom, Y [represents] representing a boron atom or a phosphorus atom, a [represents] representing an integer of 3 or more, b [represents] representing an integer of a to 2a+c+2, and c [represents] representing an integer of 1 to a.

7. (Amended) [A] The method for forming a silicon film according to claim 1, [wherein] the silicon compound is a composition containing a silicon compound represented by the following general formula [(I)] and a silicon compound represented by [the following general formula (II):]

Si_nX_m [(I)]

[wherein] n [represents] representing an integer 3 or more, m [represents] representing an integer of n, 2n-2, 2n, or 2n+2, and X [represents] representing a hydrogen atom and/or a halogen atom; and

silicon compound represented by

$Si_aX_bY_c$ [(II)]

[wherein] X [represents] representing a hydrogen atom and/or a halogen atom, Y [represents] representing a boron atom or a phosphorus atom, a [represents] representing an integer of 3 or more, b [represents] representing an integer of a to 2a+c+2, and c [represents] representing an integer of 1 to a.

8. (Amended) [A] The method for forming a silicon film according to [either] claim 5 [or 7], [wherein] n [is] being in a range of 5 to 20 [in the general formula (I)].

9. (Amended) [A] The method for forming a silicon film according to [either] claim 6 [or 7], [wherein] a+c [is] being in a range of 5 to 20 [in the general formula (II)].

10. (Amended) [A] The method for forming a silicon film according to [any one of claims 1 to 9] claim 1, [wherein, in the composition], the silicon compound [is] being dissolved in at least one solvent having a vapor pressure at room temperature of 0.001 to 50 mmHg.

11. (Amended) [A] The method for forming a silicon film according to claim 10, [wherein] the solvent [is] being a hydrocarbon solvent.

12. (Amended) [A] The method for forming a silicon film according to [any one of claims 1 to 11] claim 1, [wherein] the concentration of the silicon compound in the composition [is] being in a range of 0.01 to 10 percent by weight.

13. (Amended) [A] The method for forming a silicon film according [to any one of claims 1 to 12] claim 1, [wherein] the concentration [has] being a viscosity of 1 to 50 mPa·s and a surface tension of 20 to 70 dyn/cm.

14. (Amended) An ink-jet ink composition for forming a silicon film, comprising: a silicon compound represented [by the general formula (I):]

$$Si_nX_m \qquad [(I)]$$

[wherein] n [represents] representing an integer 3 or more, m [represents] representing an integer of n, 2n-2, 2n, or 2n+2, and X [represents] representing a hydrogen atom and/or a halogen atom.

15. (Amended) An ink-jet ink composition for forming a silicon film, comprising: a silicon compound represented by [the general formula (II):]

$$Si_aX_bY_c \qquad [(II)]$$

[wherein] X [represents] representing a hydrogen atom and/or a halogen atom, Y [represents] representing a boron atom or a phosphorus atom, a [represents] representing an integer of 3 or more, b [represents] representing an integer of a to 2a+c+2, and c [represents] representing an integer of 1 to a.

16. (Amended) An ink-jet ink composition for forming a silicon film, comprising: a silicon compound represented by [the following general formula (I) and a silicon compound represented by the following general formula (II):]

$$Si_nX_m \qquad [(I)]$$

[wherein] n [represents] representing an integer 3 or more, m [represents] representing an integer of n, 2n-2, 2n, or 2n+2, and X [represents] representing a hydrogen atom and/or a halogen atom; and

a silicon compound represented by

$$Si_aX_bY_c \qquad (II)$$

[wherein] X [represents] representing a hydrogen atom and/or a halogen atom, Y [represents] representing a boron atom or a phosphorus atom, a [represents] representing an integer of 3 or more, b [represents] representing an integer of a to 2a+c+2, and c [represents] representing an integer of 1 to a.

17. (Amended) [An] The ink composition according to [either] claim 14 [or 16], [wherein] n [is] being in a range of 5 to 20 [in the general formula (I)].

18. (Amended) [An] The ink composition according to [either] claim 15[or 16], wherein a+c [is] being in a range of 5 to 20 [in the general formula (II)].

19. (Amended) [An] The ink composition according to [any one of claims 14 to 18] claim 14, [wherein] the silicon compound [is] being dissolved in at least one solvent having a vapor pressure at room temperature of 0.001 to 50 mmHg.

20. (Amended) [An] The ink composition according to claim 19, [wherein] the solvent [is] being a hydrocarbon solvent.

21. (Amended) [An] The ink composition according to [any one of claims 14 to 20] claim 14, [wherein] the concentration of the silicon compound in the composition [is] being in a range of 0.01 to 10 percent by weight.

22. (Amended) [An] The ink composition according to [any one of claims 14 to 21] claim 14, [wherein] the concentration [has] having a viscosity of 1 to 50 mPa·s and a surface tension of 20 to 70 dyn/cm.